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BRS	BRS	BRS	BRS	BRS	BRS	Туре
L6	L5	L4	L3	12	L1	#
103	17987	736	60	51	718	Hits
4 and 5	LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or USPAT; drain\$1)) or (lightly-doped US-PGPUB adj (source\$1 or drain\$1)) EPO; JPO or ((shallow or extension\$1) near4 (source\$1 or drain\$1))	1 or 2 or 3	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or (LD adj MOSFET\$1)	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	DBs
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7	BRS	L7	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDD-MOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:03		•	0
8	BRS	L8	74	lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:04			0
. 0	BRS	L9	· 0	lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:05			0
10	BRS	L10	177	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13			0
11	BRS	L11	0	lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13			0
12	BRS	L12	716	7 or 8 or 9 or 10 or 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13			0
13	BRS	L13	497	5 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:08			0

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14	BRS	L 1 4	152128	(gate\$1 or electrode\$1) and source\$1 and drain\$1		2002/03/13 17:10	
15	BRS	L15	140632	(field adj (oxide or isolat\$5)) or LOCOS or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:29	
16	BRS	L16	197	13 and 14 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13	·
17	7 BRS	L17	140776	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13	
18	8 BRS	L20	249	lateral\$4 near7 (metal adjoxide adj semiconduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/13	

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7	מאט	177	000		DERWENT;	. (		er D	
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20	BRS	L22	2317	NMOSFET\$1 or PMOS or	DERWENT;	18:01	***************************************	•	•••••••
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21	BRS	L23	3309	or 22	EPO; JPO;	18:02			
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22	BRS	L24	991	23 and 5	EPO; JPO;	- ω ·	************		
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23	BRS	L25	G L	24 and 17 and 14	DERWENT;	18:03	•		
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L27	L26	L19	L18	L #
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26 and 17	23 and 14	LDNMOS\$2 or LD-NMOS\$2 or US-PGPUB (LD adj NMOS\$3) or LD-NMOSFET\$1 EPO; JPO LDNMOSFET\$1 or LD-NMOSFET\$1 DERWENT; or (LD adj NMOSFET\$1) IBM TDB	LDPMOS\$2 or LD-PMOS\$2 or US-PGPUB (LD adj PMOS\$3) or LD-PMOSFET\$1 EPO; JPO LDPMOSFET\$1 Or LD-PMOSFET\$1 DERWENT; or (LD adj PMOSFET\$1) IBM TDB	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	DBs
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103	17987	736	60	51	718	Hits
4 and 5	LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or USPAT; drain\$1)) or (lightly-doped US-PGPUB; adj (source\$1 or drain\$1)) EPO; JPO; or ((shallow or extension\$1) near4 (source\$1 or drain\$1))	1 or 2 or 3	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	DBs
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0			2002/03/13 17:07	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	7 or 8 or 9 or 10 or 11	716	L12	BRS	12
0			2002/03/13 17:06	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)	0	L1 1	BRS	<u> </u>
0	9		2002/03/13 17:05	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	177	110	BRS	10
0			2002/03/13 17:05	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4	Ο	L9	BRS	Ø
0			2002/03/13 17:04	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4	74	8	BRS	ω
0			2002/03/13 17:03	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDD-MOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	479	L7	BRS	7
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lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LD-NMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	14 and 15	(field adj (oxide or isolat\$5)) or LOCOS or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	(gate\$1 or electrode\$1) and source\$1 and drain\$1	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT;	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; and US-PGPUB; EPO; JPO; DERWENT; IBM TDB	DBs
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0		. 40	2002/03/13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	4 or 12 or 18 or 19 or 20 or 22	3309	L23	BRS	23
0			2002/03/13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	2317	L22	BRS	22
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